**Ultrafast Exciton and Carrier Dynamics in Bulk CrSBr**

Lawson T. Lloyd1, Tommaso Pincelli1,2, Túlio de Castro1, Ferdinand Menzel3, Zdeněk Sofer4, Nathan P. Wilson3, Martin Wolf1, Laurenz Rettig1, and Ralph Ernstorfer\*,1,2

1. Fritz-Haber-Institut der Max Planck Gesellschaft, Berlin, Germany
2. Technische Universität Berlin, Berlin, Germany
3. Walter Schottky Institut, Department of Physics, School of Natural Sciences, Technische Universität München, Garching, Germany
4. Chemistry Department, University of Chemistry and Technology Prague, 16628 Prague, Czech Republic

\* Corresponding author: ernstorfer@fhi-berlin.mpg.de

**ABSTRACT**

Van der Waals (vdW) layered magnets have the potential to enable novel optoelectronic and spintronic applications. Among these, CrSBr is a direct band gap semiconductor that hosts interlayer antiferromagnetic order, a highly anisotropic, quasi-1D electronic structure, and strongly bound excitons. However, understanding how the carrier and exciton dynamics couple to the underlying spin order is currently lackng. Here, we employ time- and angle-resolved photoemission spec- troscopy to map the temperature-dependent band structure and car- rier dynamics in bulk CrSBr. Time-resolved measurements reveal a rapid band renormalization of the lower conduction band that occurs during photoexcitation, pointing towards complex many-body effects govern- ing the excited state dynamics and optical properties. These results provide important experimental observations of the low-temperature electronic band structure and shed further light on the microscopic interactions driving carrier dynamics and spin order in this vdW mag- net.

**Introduction**

[2D Magnets etc]. CrSBr is a van der Waals layered magnetic semiconductor that with a direct electronic band gap, highly anisotropic optical and electronic properties, as well as pronounced many-body exciton physics which couple to the underlying magnetic order. (*1*–*4*) [Ultrfast] Previous time-resolved studies have uncovered coherent exciton-magnon coupling persisting to the nanosecond timescale (*2*, *5*, *6*) and as well as few to sub-picosecond exciton decay dynamics in bulk and monolayer CrSBr. (*7*)

Recently, trARPES has proved an incisive technique to directly probe the energetics and momentum distribtuino of bound excitons in a variety of systems. (*8*)

Here, we employ time- and angle-resolved photoemission (trARPES) to track the photoinduced femtosecond dynamics and directly probe the excitonic signatures in bulk CrSBr (**Figure 1**).

Physics of exciton Mott transition (*9*)

**Figure 1.** (a) E = 0 eV is referenced to the valence band maximum (VBM) peak at the point.

**Results and Discussion**

To map the electronic band structure and photoinduced dynamics of bulk CrSBr, we perform time-and angle-resolved photoemission spectroscopy (trARPES) with tunable femtosecond pump pulses. Leveraging momentum microscopy, which allows for the simultaneous acquisition of both in-plane momenta (kx, ky) and provides a global view of the electronic band structure and electronic dynamics in a single experiment (**Figure 1**). (*10*, *11*)

~~We perform ARPES at temperatures above and below the reported bulk magnetic transition temperature (T~~~~N~~ ~~~ 132 K), at which the system hosts interlayer antiferromagnetic ordering, with intralayer ferromagnetic order persisting to higher temperatures temperature (T~~~~C~~ ~~~ 165 K). (~~*~~12~~*~~)~~ **F**

**Figure 1d** shows a two-dimensional (*kx, ky*) momentum map near the valence band maximum (VBM) at room-temperature. While the central (*kx=ky=*0) point shows suppressed intensity, the point of the second Brillouin zone is more intense (*13*, *14*).

After photoexcitation (1.55 eV, ~40 fs), we observe a quasi-flat dispersion along appearing >1 eV above the valence band maximum. (**Figure 1e,f**) Such an anisotropic dispersion has been predicted theoretically and recently observed in ARPES of few-layer CrSBr in contact with metallic substrates. (*15*) Our observations of the transient electronic band structure provide further evidence of the quasi-one dimensional nature of this material. (*16*) In particular, we observe two distinct features around E ~ 1.3 eV and E ~ 2.0 eV relative to the valence band maximum, each displaying the characteristic quasi-1D band dispersion along . While initial experimental studies estimated the electronic band gap of bulk CrSBr to be around 1.5 eV, (*17*) recent ARPES works have suggested a possibly larger band gap of nearly 2 eV or greater. (*13*, *18*) Optical measurements have shown the lowest-energy exciton resonance determining the optical band gap to lie around ~1.35 eV. (*1*, *2*, *16*) Taken together, we therefore assign the two features observed in our data at E ~ 1.3 eV and E ~ 2 eV to the bound exciton state and the single-particle conduction band minimum of CrSBr, respectively. Notably, our assignment implies an exciton binding energy of at least 700 meV in bulk CrSBr, consistent with previous theoretical works and provides direct evidence of the exciton’s anisotropic nature. [] To our knowledge, a direct, momentum- and energetically resolved picture of the exciton, including its binding energy, in CrSBr has so far been lacking.

The observation of the higher energy feature at E = 2.0 eV is striking considering the pump excitation energy of 1.55 eV is below the electronic band gap based on our assignment of ~2.0 eV. **Figure 2b,c** shows the kx dispersion and the ultrafast dynamics of these two features X and CB. While there is a rapid rise of the lower energy feature, the upper feature at E = 2.0 eV exhibits a pronounced growth after photoexcitation, pointing to a dynamical process that populates this state on the ~100s fs timescale. Additionally, the dynamics of the X feature at different momenta along do not change appreciably (**Figure S**), suggesting a common origin.

To better understand the relationship between the X and CB features and the dynamics leading to the population of CB after photoexcitation, we perform further trARPES measurements with varying excitation fluence and wavelength. In particular, we pump with wavelengths close to the exciton resonance (~915 nm) as well as with wavelengths far above the band gap (400 nm). We observe change and reversal in the early-time dynamics and relative intensities of each feature such that the state CB is populated first when exciting with higher photon energies. This supports the interpretation of CB origin as the conduction band of CrSBr. Interestingly, the exciton X state, while featuring a slightly delayed rise time with respect to the CB state, is very quickly populated even with very above-gap excitation. Such a robust exciton formation could arise from the high exciton binding energy ~ 700 meV in this material and less energetically favorable dark-excitons compared to *e.g.* WSe2. (*8*)

Strong exciton-phonon coupling may also lead to enhanced phonon-assisted Auger-type decay pathways. (*19*, *20*)

The lower energy feature is more extended along whereas the higher energy feature has prominent intensity around the X points.

While these works therefore suggest an exciton binding energy of well over 0.5 eV based on photoluminescence measurements with exciton signatures of around ~1.35 eV,

Exciton formation has been shown to occur in tens of femtoseconds intransition metal dichalcogenides (*21*)

Excitation density and the Mott transition (*22*) in transition metal dichalcogenides. (*23*)

**Methods**

trARPES were performed on bulk CrSBr crystals were grown by … []. For ARPES measurements, bulk crystals were mechanically cleaved in ultrahigh vacuum in base pressures better than 10-10 mbar.

trARPES measurements were performed using both a momentum microscope and a hemispherical analyzer. For the momentum microscope measurements. using a high-repetition rate OPCPA (*24*) operating at ~500 kHz (*10*, *11*)

Previous investigations of two-dimensional semiconductors using ARPES have noted the presence of sample charging due to the photocurrent. In this work, we see clear effects of charging by a shifting of the energy scale at temperatures below T ~ 110 K, and thus we limit our measurements to temperatures above this limit.

**Author Contributions**

L.T.L, T.P., and T.d.C. performed ARPES experiments. F.M., N.P.W, Z.S. provided bulk crystal samples. M.W., L.R., and R.E. provided funding and infrastructure. L.T.L analyzed the data and wrote the manuscript with input from all authors.

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